LAPT 2SA1216

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2922)

Application : Audio and General Purpose

■ **Absolute maximum ratings** (Ta=25°C)

Symbol	Ratings	Unit
V_{CBO}	−180	V
V_{CEO}	−180	V
V_{EBO}	−5	V
I_C	−17	A
I_B	−5	A
P_C	200(Tc=25°C)	W
Tj	150	°C
Tstg	−55 to +150	°C

■ **Electrical Characteristics** (Ta=25°C)

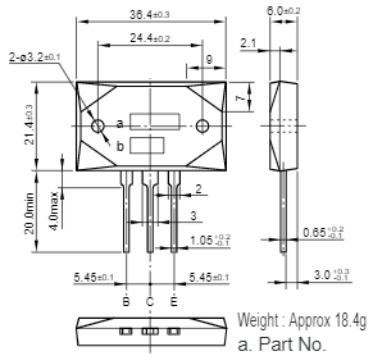
Symbol	Conditions	Ratings	Unit
V_{CBO}	V_{CB}=−180V	−100max	∝A
I_{EBO}	V_{EB}=−5V	−100max	∝A
$V_{(BR)CEO}$	I_C=−25mA	−180min	V
h_{FE}	V_{CE}=−4V, I_C=−8A	30min*	
$V_{CE(sat)}$	I_C=−8A, I_B=−0.8A	−2.0max	V
f_T	V_{CE}=−12V, I_E=2A	40typ	MHz
C_{OB}	V_{CB}=−10V, f=1MHz	500typ	pF

*h_{FE} Rank O(30to60), Y(50to100), P(70to140), G(90to180)

■ **Typical Switching Characteristics (Common Emitter)**

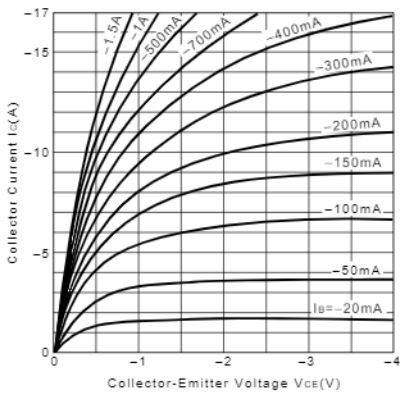
V_{CC} (V)	R_L (Ω)	I_C (A)	V_{B2} (V)	I_{B1} (A)	I_{B2} (A)	ton (∝s)	tstg (∝s)	tf (∝s)
−40	4	−10	5	−1	1	0.3typ	0.7typ	0.2typ

External Dimensions MT-200

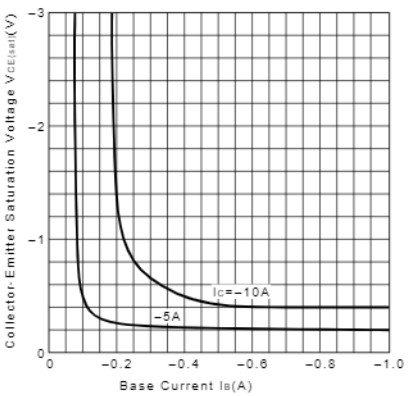


Weight : Approx 18.4g
a. Part No.
b. Lot No.

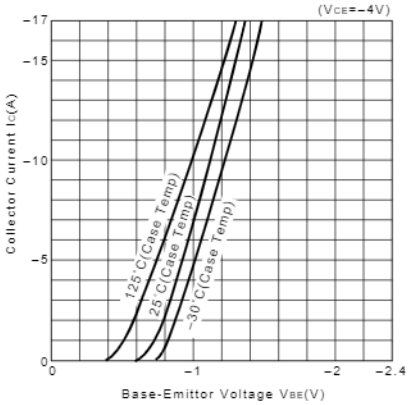
I_C−V_{CE} Characteristics (Typical)



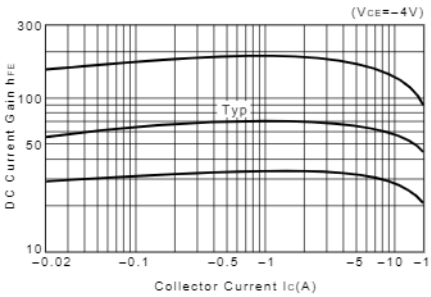
V_{CE}(sat)−I_B Characteristics (Typical)



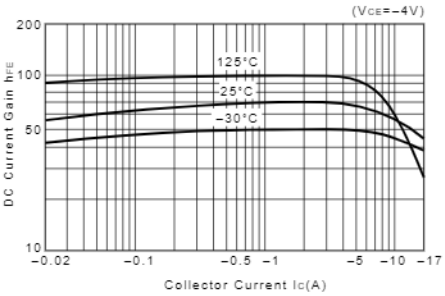
I_C−V_{BE} Temperature Characteristics (Typical)



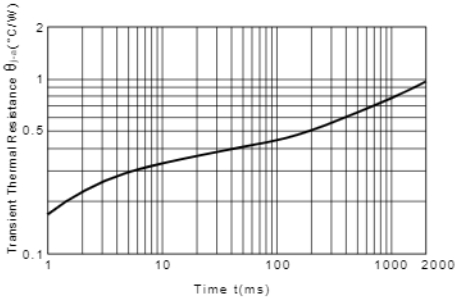
h_{FE}−I_C Characteristics (Typical)



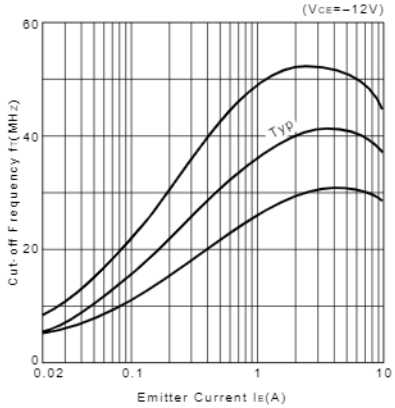
h_{FE}−I_C Temperature Characteristics (Typical)



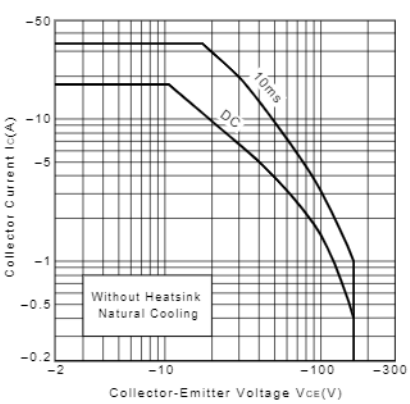
$\theta_{j\text{-}a}$−t Characteristics



f_T−I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc−Ta Derating

